

1.0 AMP FAST RECOVERY RECTIFIERS

1F1 THRU 1F7 Vishaymas General Semiconductor

FEATURES

- Low forward voltage drop
- High current capability
- High reliability
- High surge current capability

MECHANICAL DATA

Case: Molded plastic

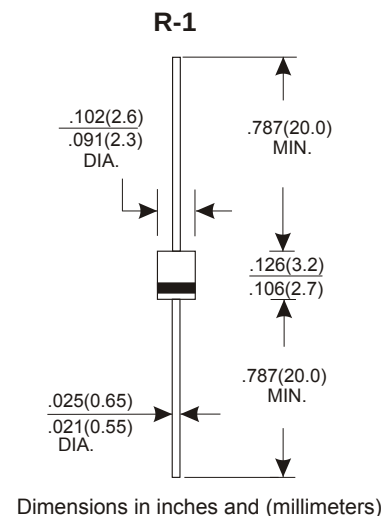
Epoxy: UL 94V-0 rate flame retardant

Lead: Axial leads, solderable per
MIL-STD-202, method 208 guaranteed

Polarity: Color band denotes cathode end

Mounting position: Any

Weight: 0.19 grams



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Rating 25°C ambient temperature unless otherwise specified. Single phase half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

TYPE NUMBER	1F1	1F2	1F3	1F4	1F5	1F6	1F7	UNITS
Maximum Recurrent Peak Reverse Voltage	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current .375"(9.5mm) Lead Length at Ta=25°C	1.0							A
Peak Forward Surge Current, 8.3 ms single half sine-wave superimposed on rated load (JEDEC method)	25							A
Maximum Instantaneous Forward Voltage at 1.0A	1.3							V
Maximum DC Reverse Current Ta=25°C	5.0							mA
at Rated DC Blocking Voltage Ta=100°C	100							mA
Maximum Reverse Recovery Time (Note 1)	150				250	500		nS
Typical Junction Capacitance (Note 2)	15							pF
Operating and Storage Temperature Range Tj, TSTG	-65 — +150							°C

NOTES:

1. Reverse Recovery Time test condition: IF=0.5A, IR=1.0A, IRR=0.25A
2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

FIG.1-TYPICAL FORWARD CHARACTERISTICS

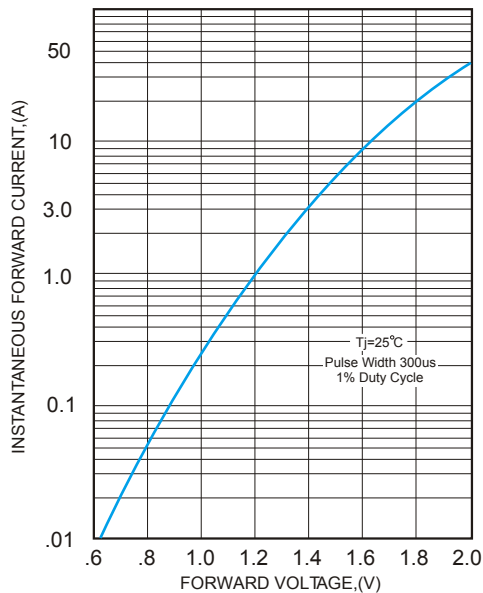
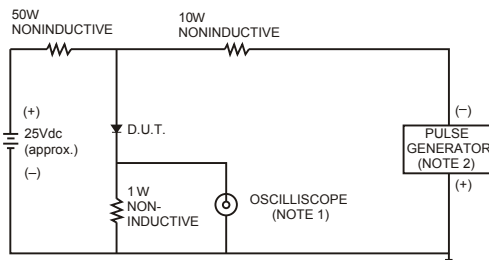


FIG.3- TEST CIRCUIT DIAGRAM AND REVERSE RECOVERY TIME CHARACTERISTICS



NOTES: 1. Rise Time= 7ns max., Input Impedance= 1 megohm, 22pF.
2. Rise Time= 10ns max., Source Impedance= 50 ohms.

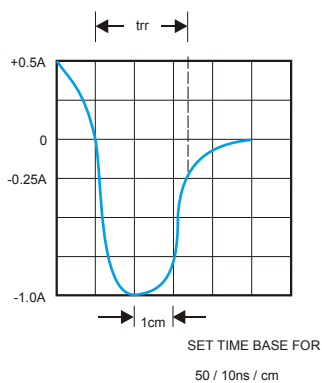


FIG.2-TYPICAL FORWARD CURRENT DERATING CURVE

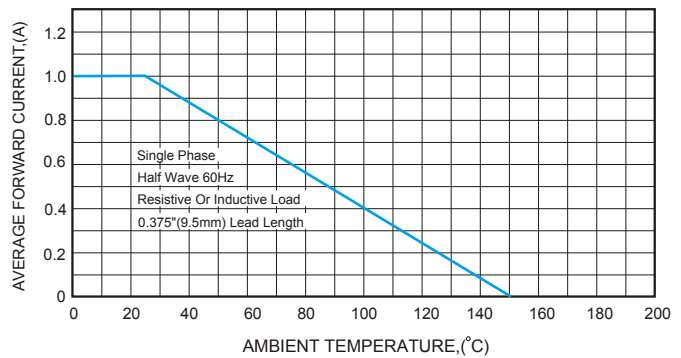


FIG.4-MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

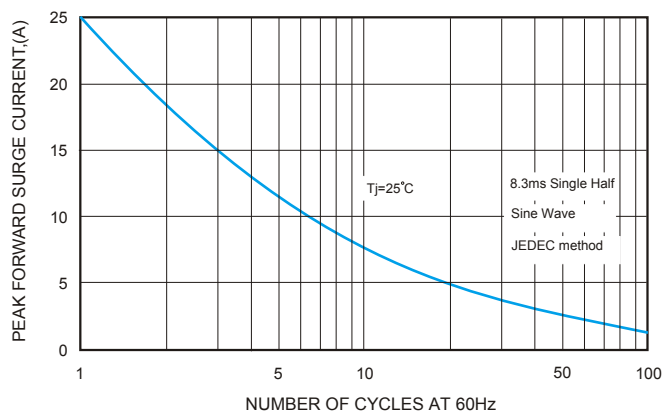


FIG.5-TYPICAL JUNCTION CAPACITANCE

